

NTMFS4707N

Power MOSFET

30 V, 17 A, Single N-Channel,
SO-8 Flat Lead

Features

- Fast Switching Times
- Low Gate Charge
- Low $R_{DS(on)}$
- Low Inductance SO-8 Package

Applications

- Notebooks, Graphics Cards
- DC-DC Converters
- Synchronous Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$	10.2	A
			$T_A = 85^\circ\text{C}$	7.4	
	$t \leq 10$ s	$T_A = 25^\circ\text{C}$	17		
Power Dissipation (Note 1)	Steady State	P_D	$T_A = 25^\circ\text{C}$	2.3	W
	$t \leq 10$ s			6.25	
Continuous Drain Current (Note 2)	Steady State	I_D	$T_A = 25^\circ\text{C}$	6.9	A
			$T_A = 85^\circ\text{C}$	4.9	
			$T_A = 25^\circ\text{C}$	1.0	
Power Dissipation (Note 2)		P_D	1.0	W	
Pulsed Drain Current	$t_p \leq 10$ μs	I_{DM}	51	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	6.25	A	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 25$ V, $V_{GS} = 10$ V, $I_{PK} = 7.0$ A, $L = 10$ mH, $R_G = 25$ Ω)		E_{AS}	245	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	55	$^\circ\text{C/W}$
Junction-to-Ambient - $t \leq 10$ s (Note 1)	$R_{\theta JA}$	20	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	122.5	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 0.412 in sq).

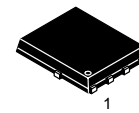
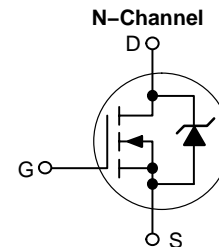


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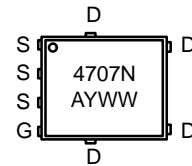
http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
30 V	10 m Ω @ 10 V	17 A
	13.5 m Ω @ 4.5 V	



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



4707N = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4707NT1G	SO-8 FL (Pb-Free)	1500 Tape & Reel
NTMFS4707NT3G	SO-8 FL (Pb-Free)	5000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFS4707N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			6.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1.0	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			5.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		10	13	mΩ
		V _{GS} = 4.5 V, I _D = 8.0 A		13.5	17	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 10 A		20		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 24 V		735		pF
Output Capacitance	C _{OSS}			295		
Reverse Transfer Capacitance	C _{RSS}			80		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 10 A		7.5	15	nC
Threshold Gate Charge	Q _{G(TH)}			1.1		
Gate-to-Source Charge	Q _{GS}			2.0		
Gate-to-Drain Charge	Q _{GD}			3.6		
Gate Resistance	R _G			2.4		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 15 V, I _D = 1.0 A, R _G = 3.0 Ω		6.0		ns
Rise Time	t _r			5.0		
Turn-Off Delay Time	t _{d(off)}			19		
Fall Time	t _f			11		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 6.25 A	T _J = 25°C		0.79	1.0	V
			T _J = 125°C		0.59		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 6.25 A		26		ns	
Charge Time	t _a			14			
Discharge Time	t _b			12			
Reverse Recovery Charge	Q _{RR}			19			nC

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERIZATIONS

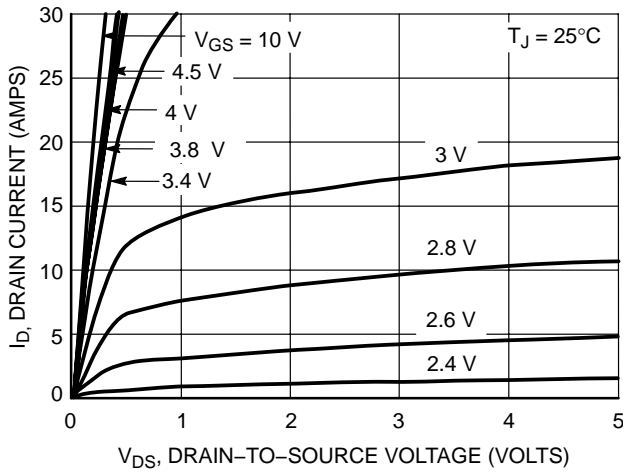


Figure 1. On-Region Characteristics

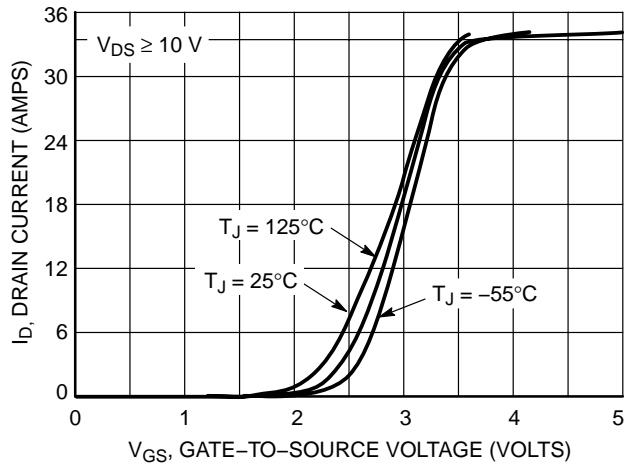


Figure 2. Transfer Characteristics

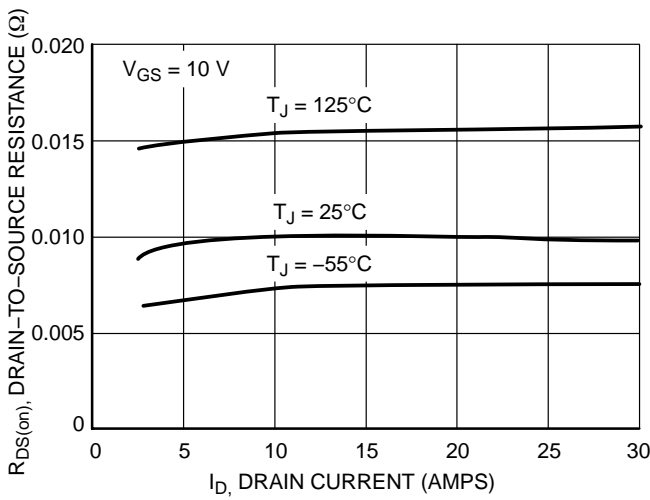


Figure 3. On-Resistance vs. Drain Current and Temperature

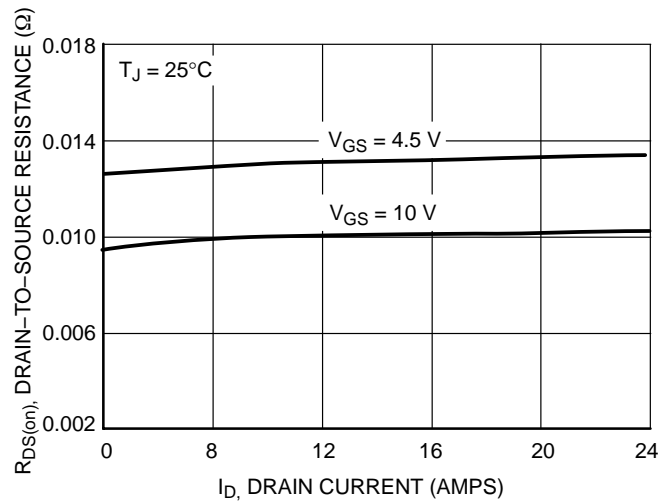


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

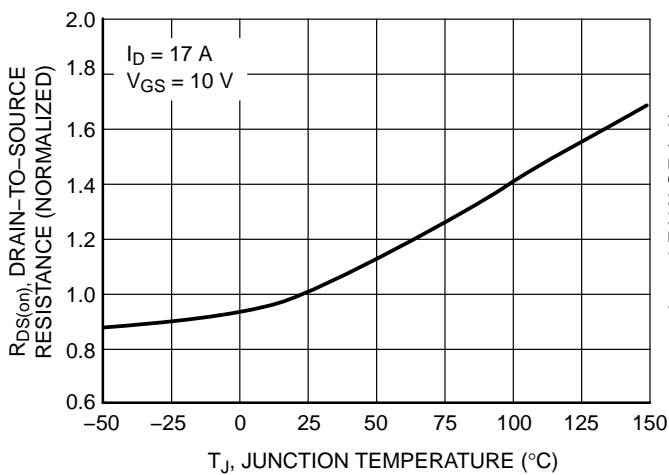


Figure 5. On-Resistance Variation with Temperature

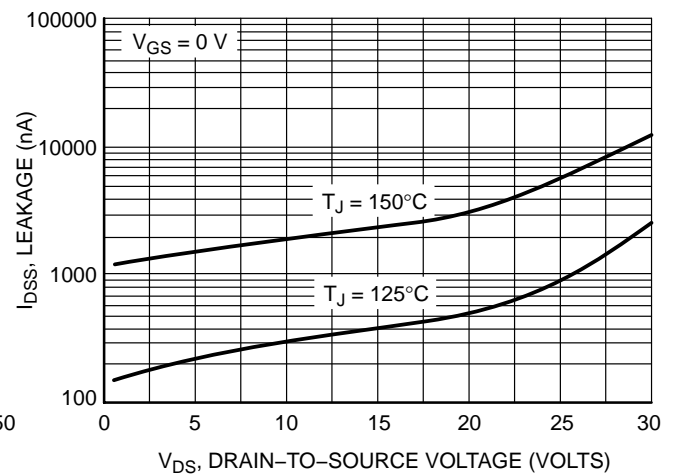


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERIZATIONS

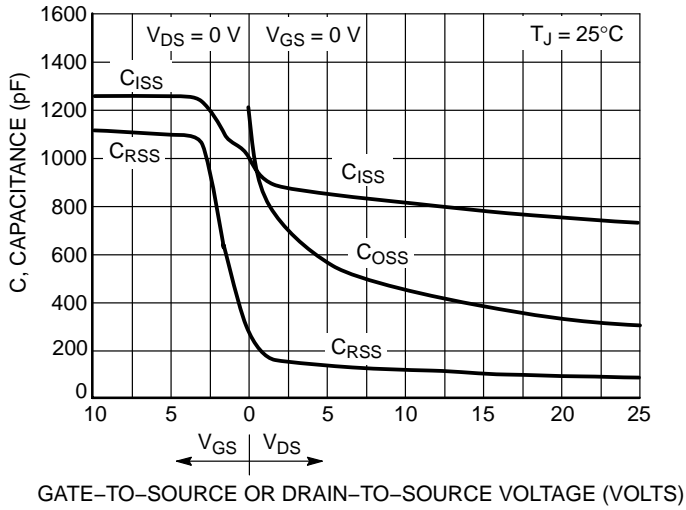


Figure 7. Capacitance Variation

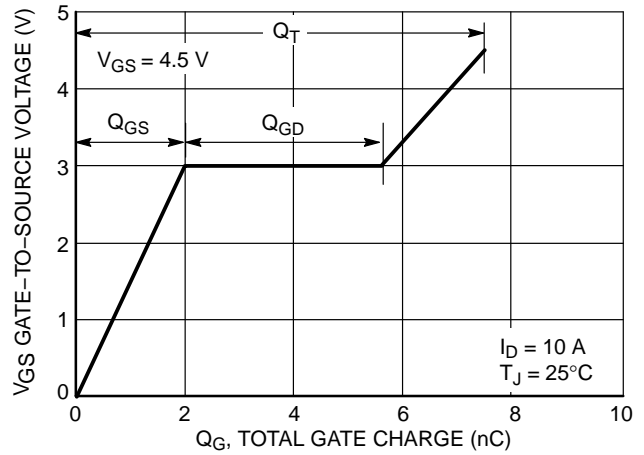


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

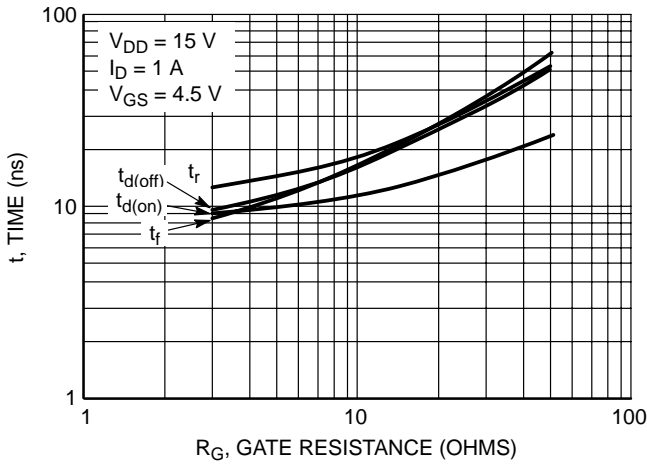


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

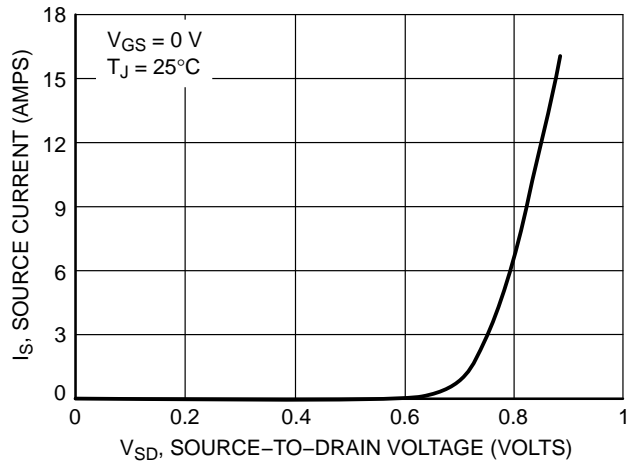


Figure 10. Diode Forward Voltage vs. Current

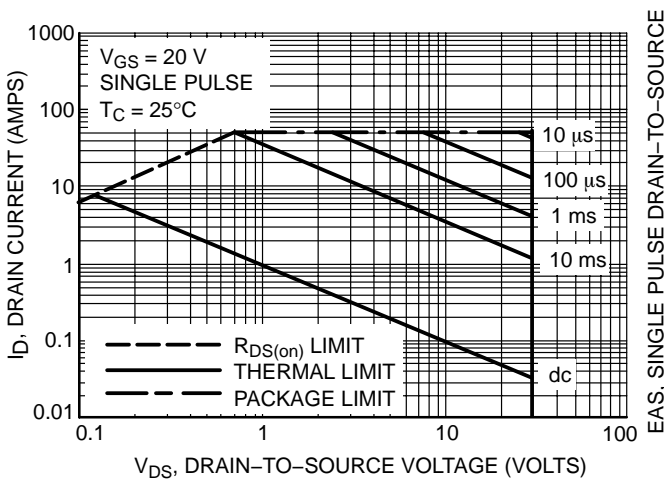


Figure 11. Maximum Rated Forward Biased Safe Operating Area

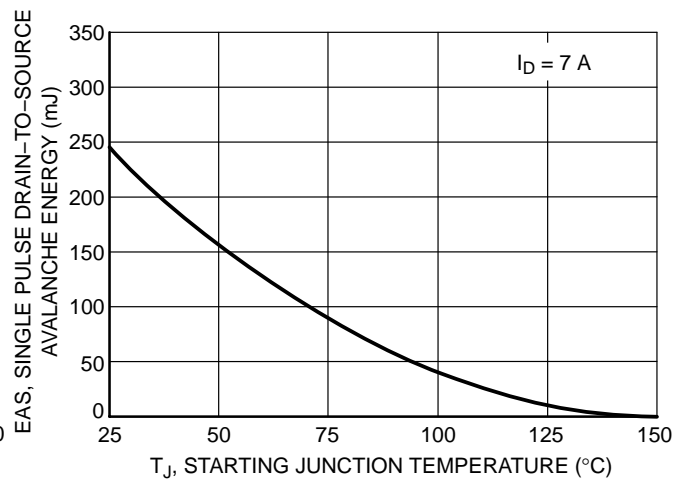


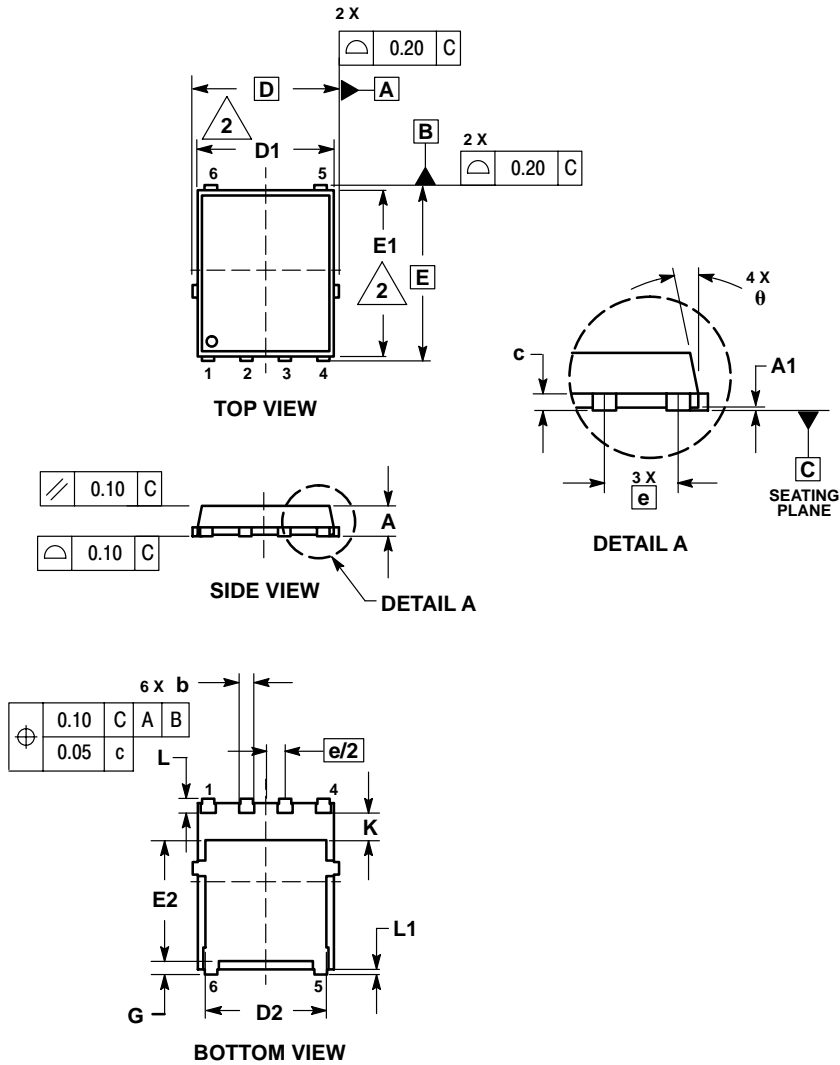
Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTMFS4707N

PACKAGE DIMENSIONS

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SO-8 FLAT LEAD
CASE 488AA-01
ISSUE A




NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	0.99	1.20
A1	0.00	----	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.50	4.90	5.10
D2	3.50	----	4.22
E	6.15 BSC		
E1	5.50	5.80	6.10
E2	3.45	----	4.30
e	1.27 BSC		
G	0.51	0.61	0.71
K	0.51	----	----
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
θ	0°	----	12°

STYLE 1:

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN
- DRAIN

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